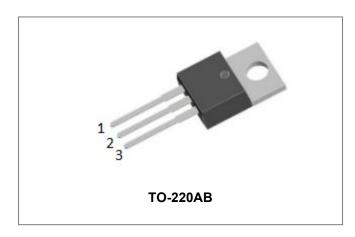






MBR20135CT/MBR20150CT SCHOTTKY RECTIFIER



Features

- 175°C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced
- · mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Terminals finish: 100% Pure Tin
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings:

Characteristics	Symbol	Condition		Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage	VRRM	-	135	MBR20135CT	W
DC Blocking Voltage	$egin{array}{c} egin{array}{c} \egin{array}{c} \egin{array}{c} \egin{array}{c} \egin{array}$		150	MBR20150CT	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @Tc=145°C,	10(Per Leg)		Α
7 (Vorago i Cottillou i Griwaru Gurront		rectangular wave form	20(Per Device)		
Peak Repetitive Surge current (Rated V _R , Square Wave,20KHz)	I _{RRM}	-	1.0		Α
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I _{FSM}	8.3ms, Half Sine pulse, T _C = 25 °C	150		Α

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop(Per Leg)*	V _{F1}	@ 10A, Pulse, T _J = 25 °C	0.84	0.90	V
	V_{F2}	@ 10A, Pulse, T _J = 125 °C	0.75	0.83	V
Reverse Current(Per Leg)*	I _{R1}	@V _R = rated V _R , T _J = 25 °C	0.001	0.5	mA
	I _{R2}	$@V_R = rated V_R, T_J = 125 ^{\circ}C$	0.1	5	mA
Junction Capacitance(Per Leg)	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	170	400	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

Pulse width < 300 μs, duty cycle < 2%

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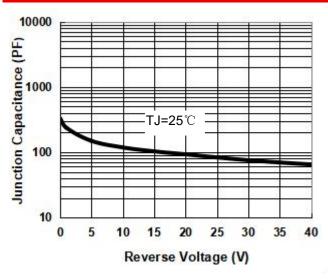




Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +175	°C
Storage Temperature	T _{stg}	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case	R _{θJC}	DC operation	1.5	°C/W
Typical Thermal Resistance, Case to Heat Sink	R _{θCS}	Mounting surface, smooth and greased	0.50	°C/W
Approximate Weight	wt	-	2	g

Ratings and Characteristics Curves



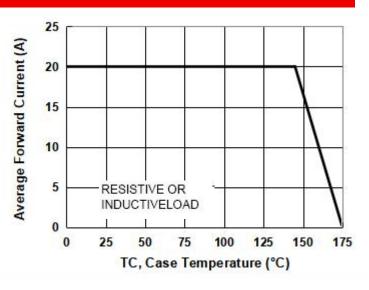


Fig.1-Typical Junction Capacitance

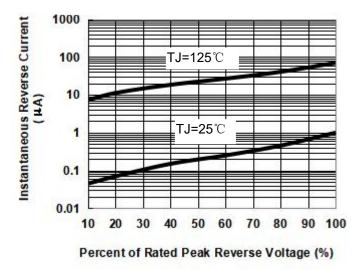


Fig.2-Forward Current Derating Curve

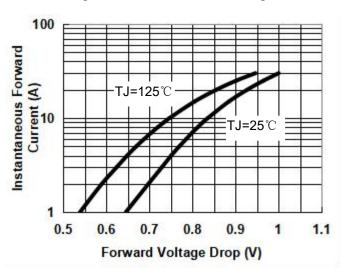


Fig.3-Typical Reverse Characteristics

Fig.4-Typica Forward Voltage Characteristics

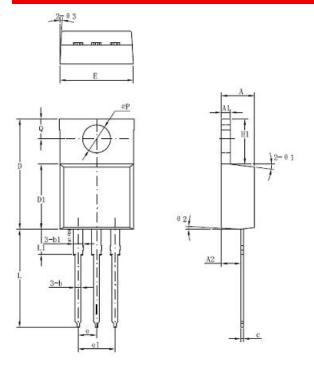
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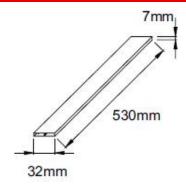


Mechanical Dimensions TO-220AB



Symbol	Dimensions in millimeters				
	Min	Typical	Max		
Α	3.56	-	4.83		
A1	0.51	-	1.40		
A2	2.03	-	2.92		
b	0.38	-	1.02		
b1	1.14	-	1.78		
С	0.31	-	0.61		
D	14.22	-	16.51		
D1	8.38	-	9.42		
E	9.65	-	10.67		
е	-	2.54	-		
e1	-	5.08	-		
H1	5.84	-	6.86		
L	12.70	-	14.73		
L1	-	-	6.35		
ФР	-	3.56	-		
Q	2.54	-	3.43		

Tube Specification



Marking Diagram



Where XXXXX is YYWWL

MBR = Device Type 20 = Forward Current (20A) 135/150 = Reverse Voltage(135/150V)

 CT
 = Configuration

 SSG
 = SSG

 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

Ordering Information

Device	Package	Shipping	
MBR20135/150CT	TO-220AB (Pb-Free)	50 pcs/ tube	

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